



FIG. 1

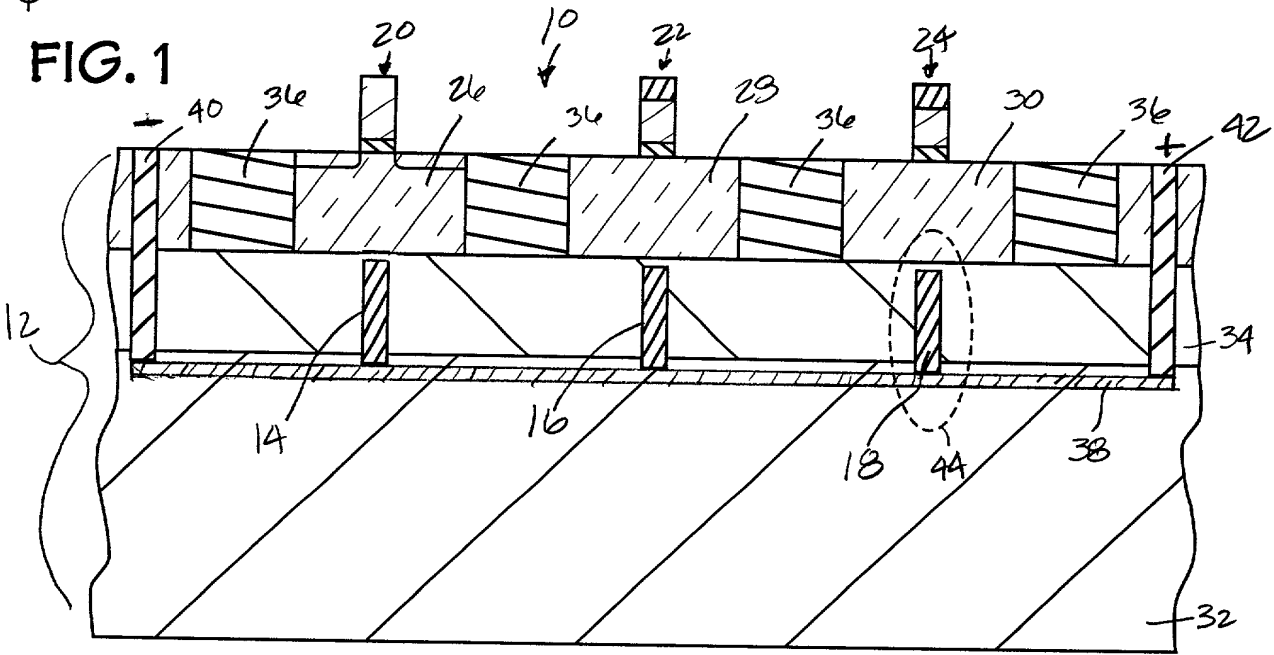


FIG. 2

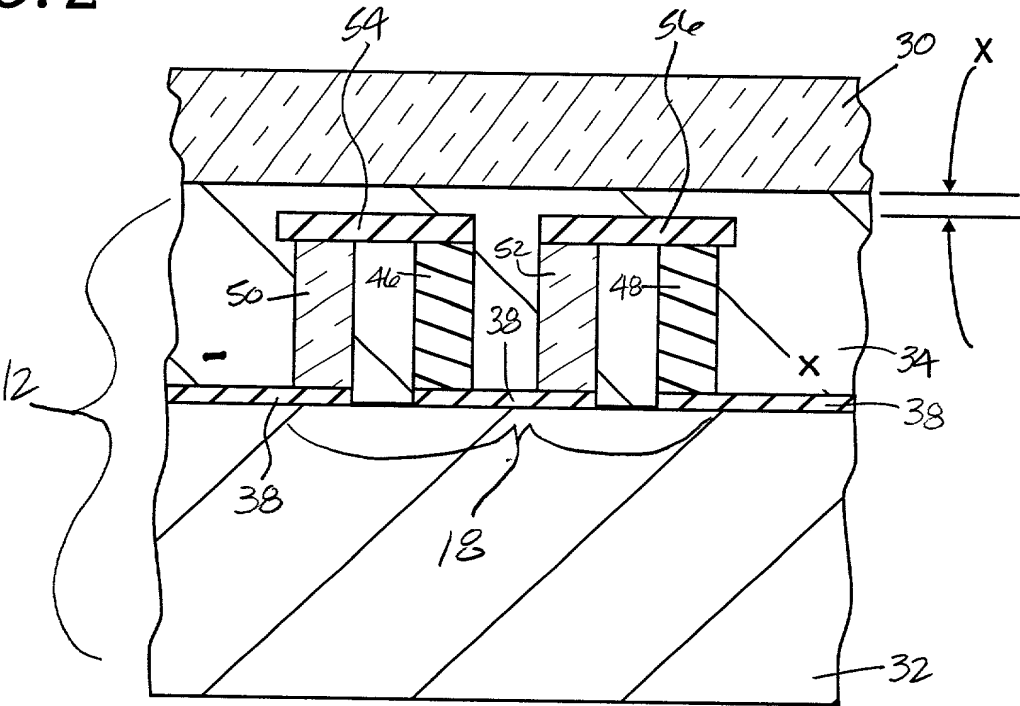




FIG. 3

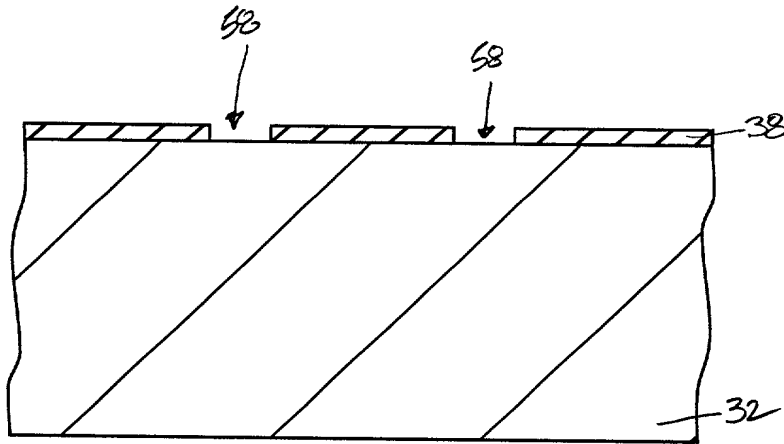


FIG. 3 is a cross-sectional view of a substrate 32 with a top layer 38. The top layer 38 has two notches 52 and 58. The substrate 32 is indicated by diagonal hatching lines.

FIG. 4

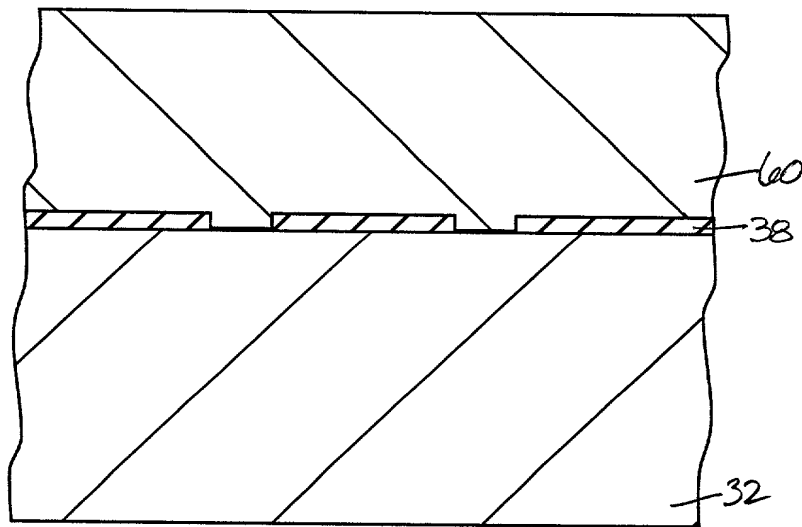




FIG. 5

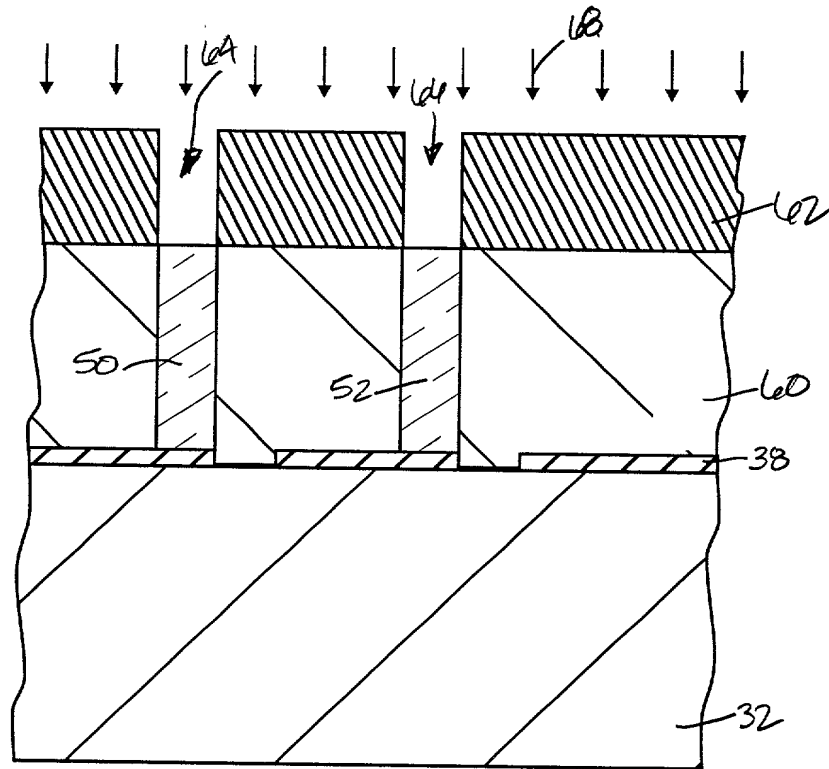


FIG. 6

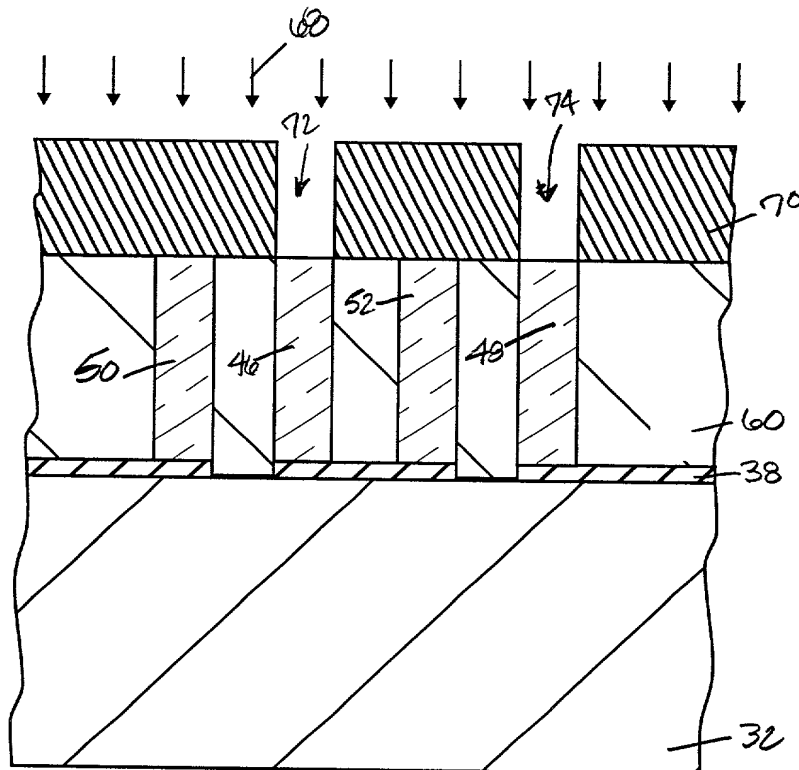




FIG. 7

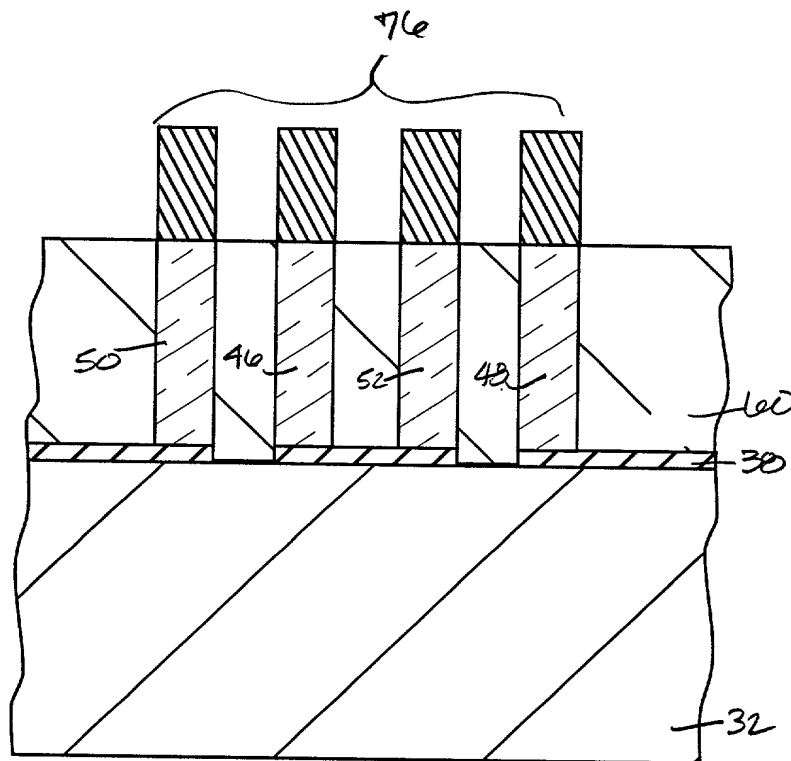


FIG. 8

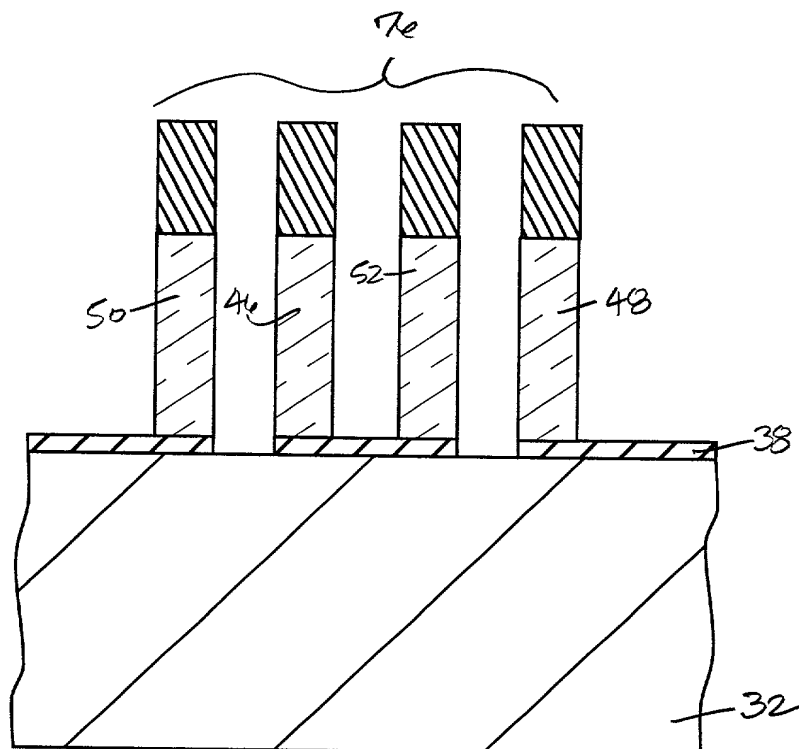




FIG. 9

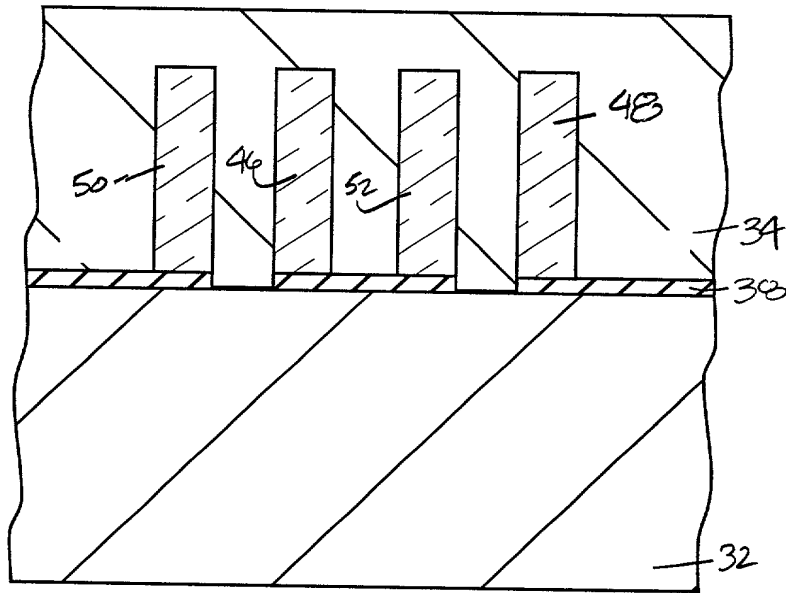


FIG. 9 is a cross-sectional view of a semiconductor device. The device includes a substrate 32, a top layer 34, and a horizontal layer 38. Four vertical structures are formed on the top layer 34. The first structure is labeled 50, the second 46, the third 52, and the fourth 48. The structures 50, 46, and 52 are shown as hatched rectangles, while structure 48 is shown as a solid rectangle. The structures 50, 46, and 52 are positioned to the left of structure 48.

FIG. 10

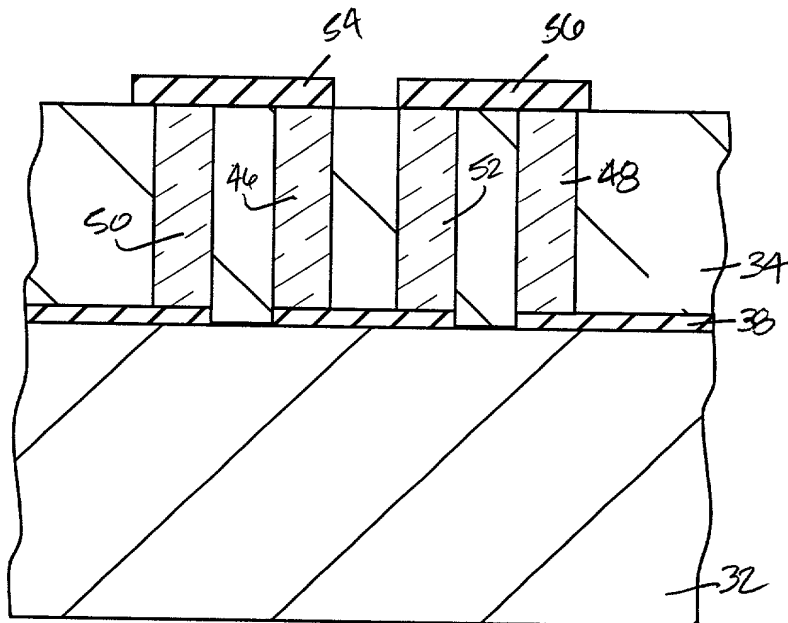




FIG. 11

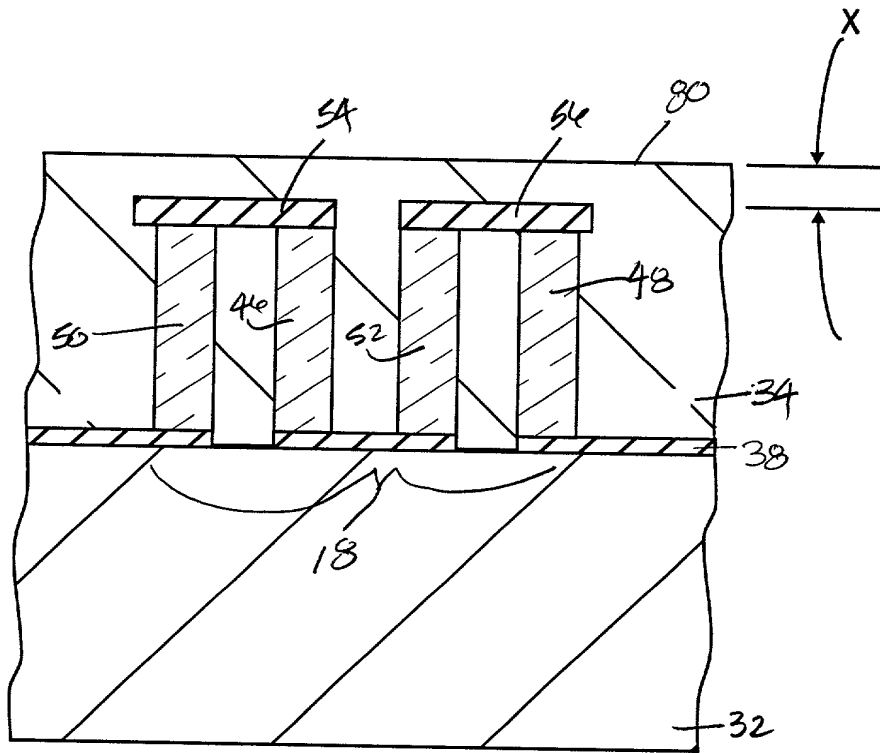


FIG. 12

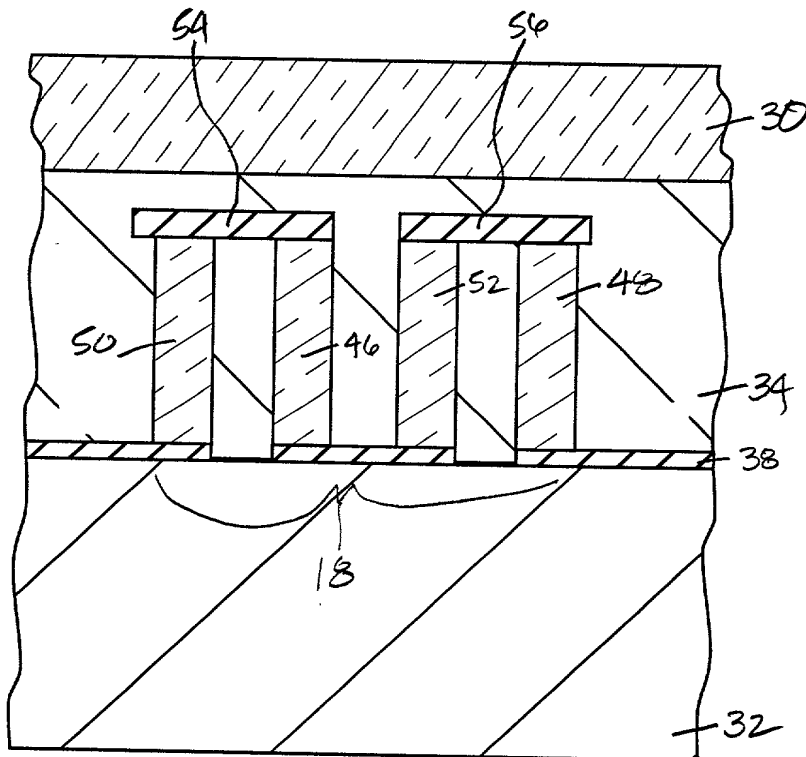




FIG. 13

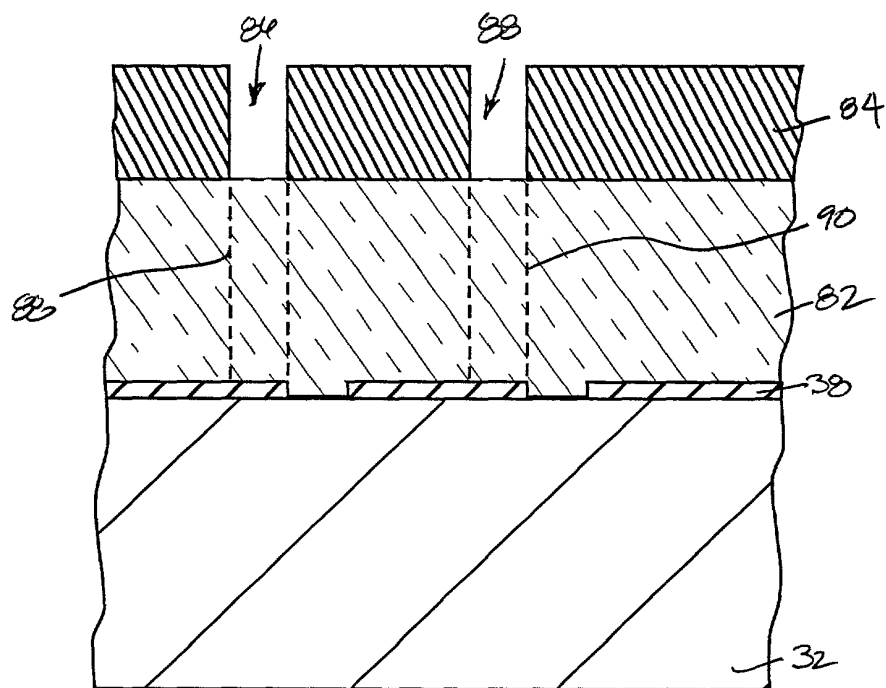


FIG. 14

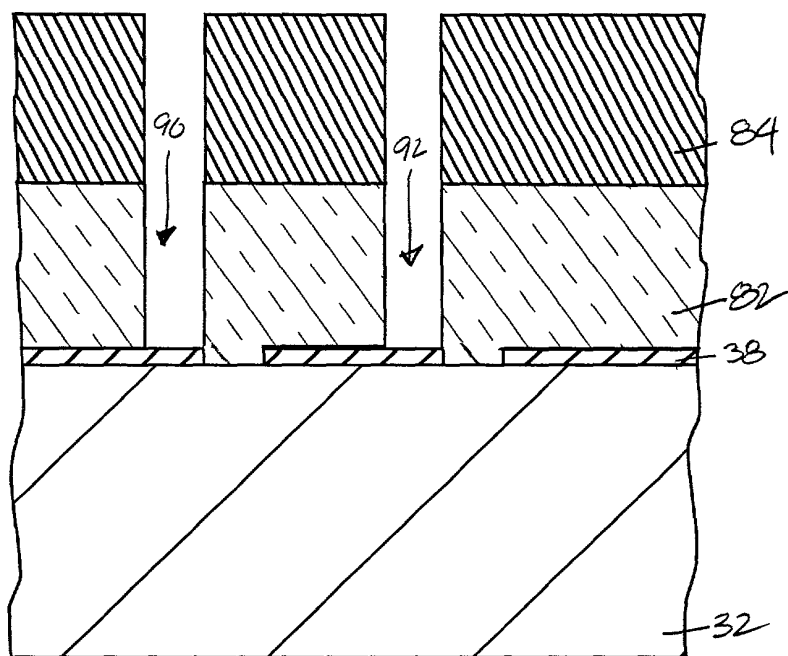




FIG. 15

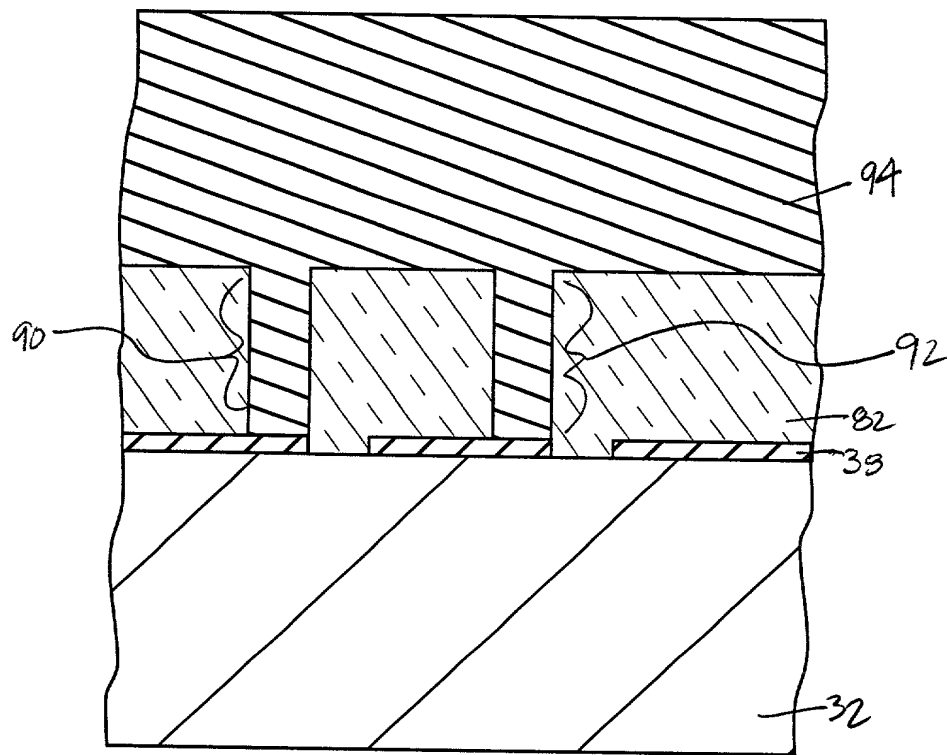


FIG. 15 is a cross-sectional view of a device structure. The top layer is labeled 94 and has diagonal hatching. Below it is a layer labeled 90, which contains three rectangular blocks. The blocks are separated by gaps. The rightmost block is labeled 92. Below the blocks is a thin layer labeled 82, which is hatched with diagonal lines. Below layer 82 is a layer labeled 33, which is also hatched with diagonal lines. The bottom layer is labeled 32 and has diagonal hatching. The entire structure is shown in a cross-sectional view.

FIG. 16

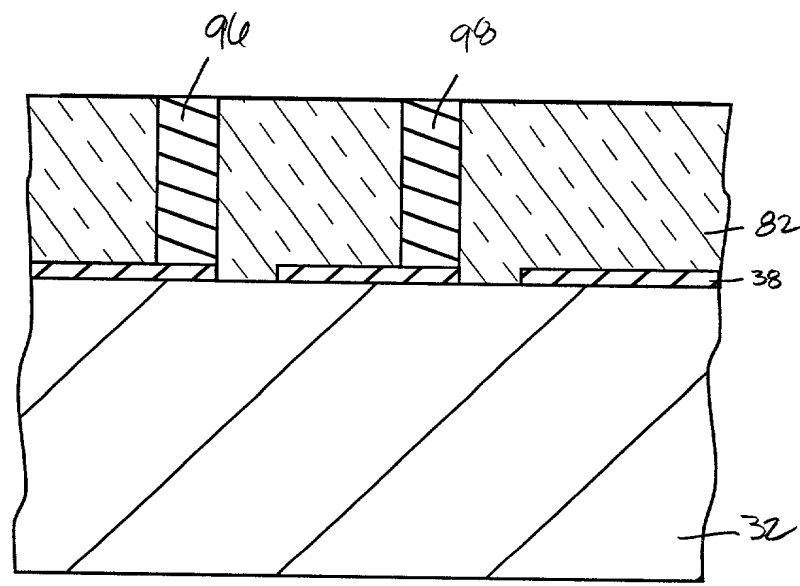






FIG. 17

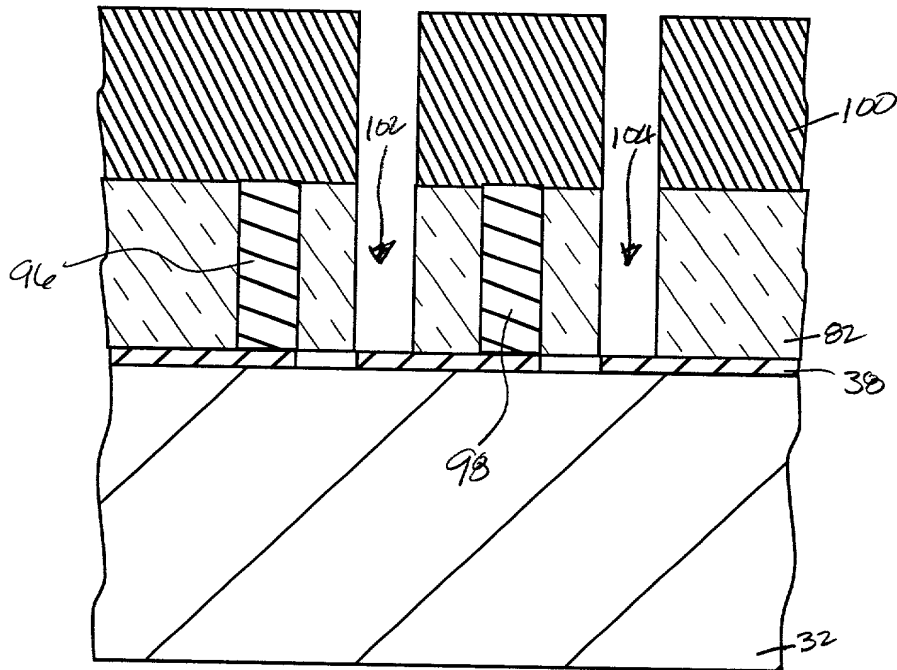


FIG. 17 is a cross-sectional view of a semiconductor device. The device includes a substrate 32, a layer 38, a layer 82, and three vertical structures 96. Each structure 96 has a central core 102 and side regions 104. The top of the device is covered by a layer 100.

FIG. 18

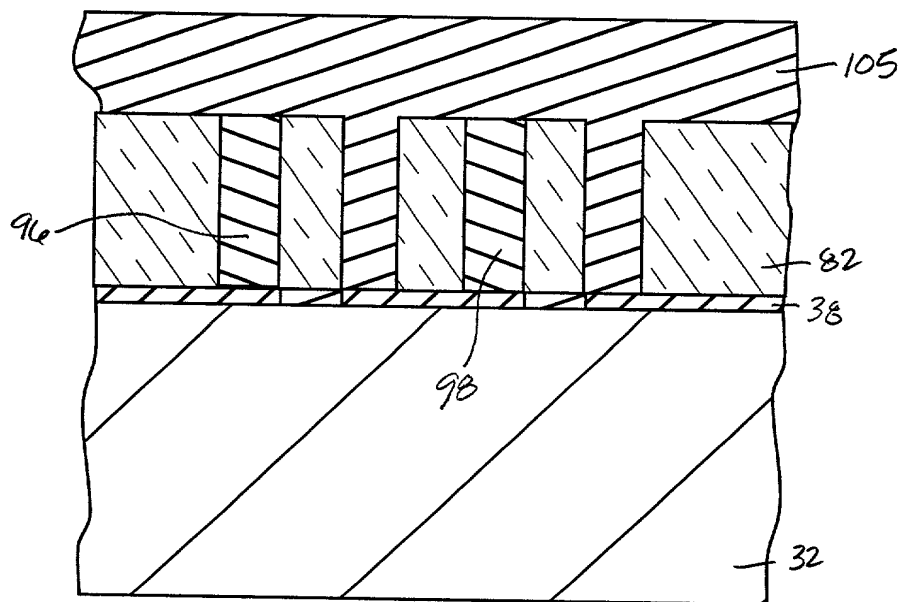




FIG. 19

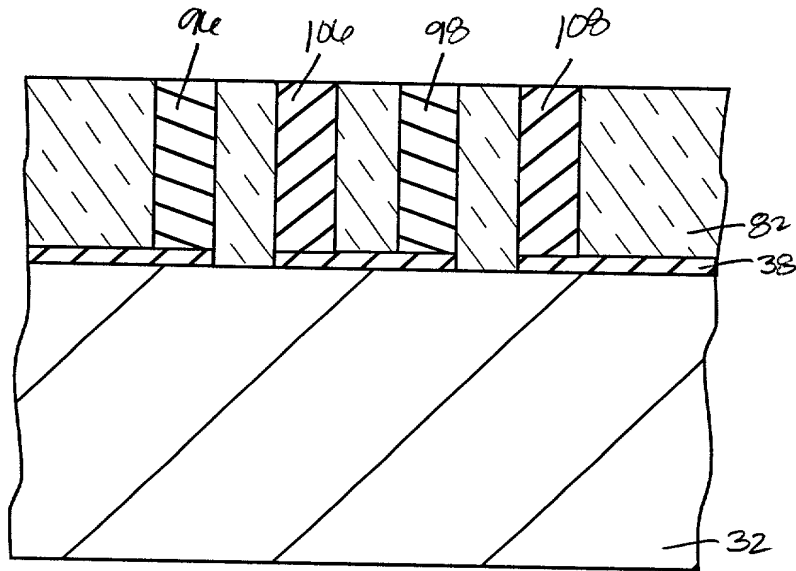


FIG. 20

